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What is "Embedded - Microcontrollers"?

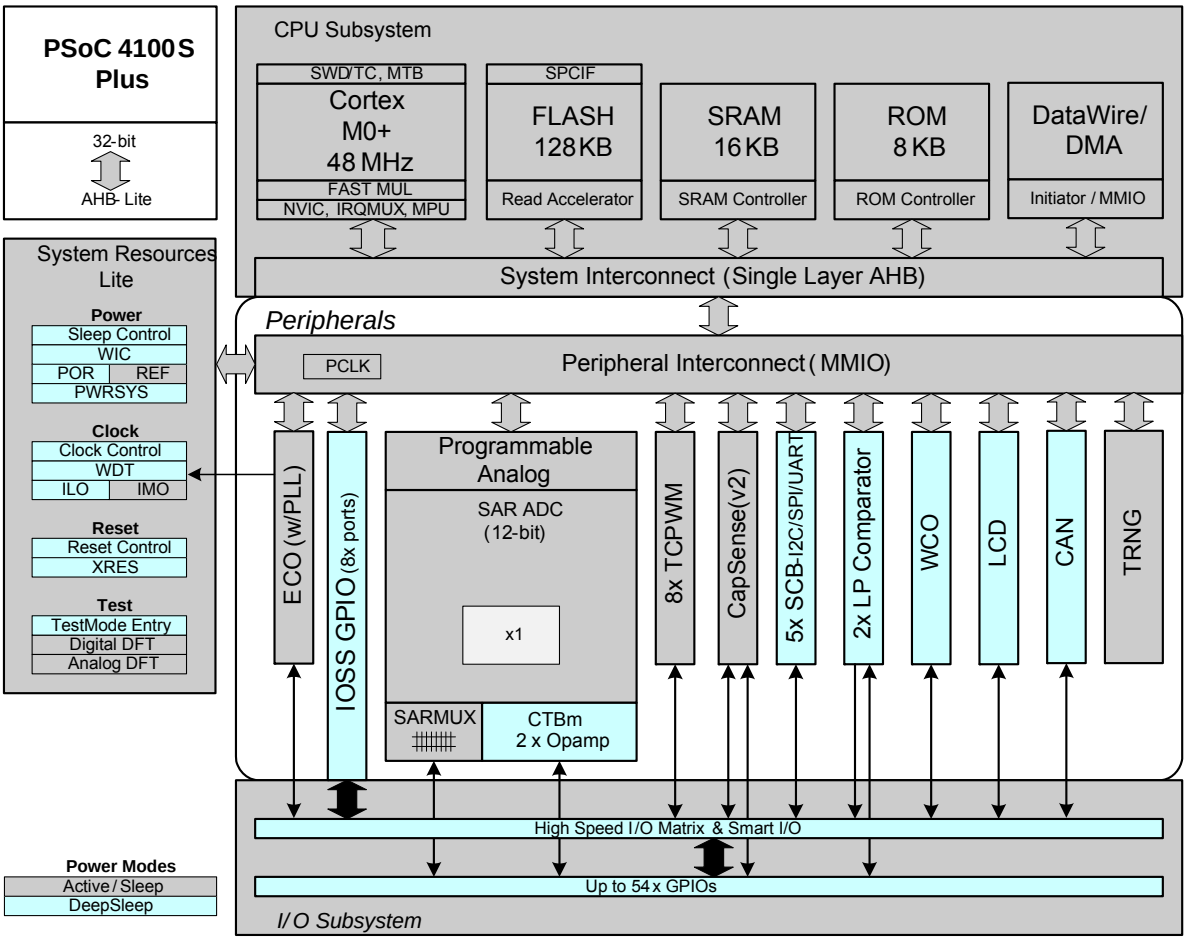
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Brown-out Detect/Reset, CapSense, LCD, POR, PWM, WDT
Number of I/O	54
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x10b Slope, 16x12b SAR; D/A 2xIDAC
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4147axi-s445

Contents

Figure 2. Block Diagram



PSoC 4100S Plus devices include extensive support for programming, testing, debugging, and tracing both hardware and firmware.

The Arm Serial-Wire Debug (SWD) interface supports all programming and debug features of the device.

Complete debug-on-chip functionality enables full-device debugging in the final system using the standard production device. It does not require special interfaces, debugging pods, simulators, or emulators. Only the standard programming connections are required to fully support debug.

The PSoC Creator IDE provides fully integrated programming and debug support for the PSoC 4100S Plus devices. The SWD interface is fully compatible with industry-standard third-party tools. PSoC 4100S Plus provides a level of security not possible with multi-chip application solutions or with microcontrollers. It has the following advantages:

- Allows disabling of debug features
- Robust flash protection
- Allows customer-proprietary functionality to be implemented in on-chip programmable blocks

The debug circuits are enabled by default and can be disabled in firmware. If they are not enabled, the only way to re-enable them is to erase the entire device, clear flash protection, and reprogram the device with new firmware that enables debugging. Thus firmware control of debugging cannot be over-ridden without erasing the firmware thus providing security.

Additionally, all device interfaces can be permanently disabled (device security) for applications concerned about phishing attacks due to a maliciously reprogrammed device or attempts to defeat security by starting and interrupting flash programming sequences. All programming, debug, and test interfaces are disabled when maximum device security is enabled. Therefore, PSoC 4100S Plus, with device security enabled, may not be returned for failure analysis. This is a trade-off the PSoC 4100S Plus allows the customer to make.

Pinouts

The following table provides the pin list for PSoC 4100S Plus for the 44-pin TQFP and 64-pin TQFP Normal and Fine Pitch packages.

64-TQFP		44-TQFP	
Pin	**Name**	**Pin**	**Name**
39	P0.0	24	P0.0
40	P0.1	25	P0.1
41	P0.2	26	P0.2
42	P0.3	27	P0.3
43	P0.4	28	P0.4
44	P0.5	29	P0.5
45	P0.6	30	P0.6
46	P0.7	31	P0.7
47	XRES	32	XRES
48	VCCD	33	VCCD
49	VSSD		
50	VDDD	34	VDDD
51	P5.0		
52	P5.1		
53	P5.2		
54	P5.3		
55	P5.5		
56	VDDA	35	VDDA
57	VSSA	36	VSSA
58	P1.0	37	P1.0
59	P1.1	38	P1.1
60	P1.2	39	P1.2
61	P1.3	40	P1.3
62	P1.4	41	P1.4
63	P1.5	42	P1.5
64	P1.6	43	P1.6
1	P1.7	44	P1.7
		1	VSSD
2	P2.0	2	P2.0
3	P2.1	3	P2.1
4	P2.2	4	P2.2
5	P2.3	5	P2.3
6	P2.4	6	P2.4
7	P2.5	7	P2.5
8	P2.6	8	P2.6
9	P2.7	9	P2.7
10	VSSD	10	P6.0
11	No Connect (NC)		
12	P6.0		
13	P6.1		

64-TQFP		44-TQFP	
Pin	**Name**	**Pin**	**Name**
14	P6.2		
15	P6.4		
16	P6.5		
17	VSSD		
17	VSSD		
18	P3.0	11	P3.0
19	P3.1	12	P3.1
20	P3.2	13	P3.2
21	P3.3	14	P3.3
22	P3.4	15	P3.4
23	P3.5	16	P3.5
24	P3.6	17	P3.6
25	P3.7	18	P3.7
26	VDDD	19	VDDD
27	P4.0	20	P4.0
28	P4.1	21	P4.1
29	P4.2	22	P4.2
30	P4.3	23	P4.3
31	P4.4		
32	P4.5		
33	P4.6		
34	P4.7		
35	P5.6		
36	P5.7		
37	P7.0		
38	P7.1		

Descriptions of the Power pins are as follows:

VDDD: Power supply for the digital section.

VDDA: Power supply for the analog section.

VSSD, VSSA: Ground pins for the digital and analog sections respectively.

VCCD: Regulated digital supply (1.8 V ±5%)

VDD: Power supply to all sections of the chip

VSS: Ground for all sections of the chip

GPIOs by package:

	64 TQFP	44 TQFP
Number	54	37

Electrical Specifications

Absolute Maximum Ratings

Table 1. Absolute Maximum Ratings[1]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID1	V_{DDD_ABS}	Digital supply relative to V_{SS}	–0.5	–	6	V	–
SID2	V_{CCD_ABS}	Direct digital core voltage input relative to V_{SS}	–0.5	–	1.95		–
SID3	V_{GPIO_ABS}	GPIO voltage	–0.5	–	V_{DD}+0.5		–
SID4	I_{GPIO_ABS}	Maximum current per GPIO	–25	–	25	mA	–
SID5	$I_{GPIO\_injection}$	GPIO injection current, Max for V_{IH} > V_{DDD}, and Min for V_{IL} < V_{SS}	–0.5	–	0.5		Current injected per pin
BID44	ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	–
BID45	ESD_CDM	Electrostatic discharge charged device model	500	–	–		–
BID46	LU	Pin current for latch-up	–140	–	140	mA	–

Device Level Specifications

All specifications are valid for –40 °C ≤ T_A ≤ 85 °C and T_J ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 2. DC Specifications

Typical values measured at V_{DD} = 3.3 V and 25 °C.

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID53	V_{DD}	Power supply input voltage	1.8	–	5.5	V	Internally regulated supply
SID255	V_{DD}	Power supply input voltage (V_{CCD} = V_{DDD} = V_{DDA})	1.71	–	1.89		Internally unregulated supply
SID54	V_{CCD}	Output voltage (for core logic)	–	1.8	–		–
SID55	C_{EFC}	External regulator voltage bypass	–	0.1	–	µF	X5R ceramic or better
SID56	C_{EXC}	Power supply bypass capacitor	–	1	–		X5R ceramic or better
Active Mode, V_{DD} = 1.8 V to 5.5 V. Typical values measured at VDD = 3.3 V and 25 °C.							
SID10	I_{DD5}	Execute from flash; CPU at 6 MHz	–	1.8	2.4	mA	Max is at 85 °C and 5.5 V
SID16	I_{DD8}	Execute from flash; CPU at 24 MHz	–	3.0	4.6		Max is at 85 °C and 5.5 V
SID19	I_{DD11}	Execute from flash; CPU at 48 MHz	–	5.4	7.1		Max is at 85 °C and 5.5 V

Note
1. Usage above the absolute maximum conditions listed in Table 1 may cause permanent damage to the device. Exposure to Absolute Maximum conditions for extended periods of time may affect device reliability. The Maximum Storage Temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below Absolute Maximum conditions but above normal operating conditions, the device may not operate to specification.

GPIO

Table 4. GPIO DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID57	V_{IH}[3]	Input voltage high threshold	0.7 × V_{DDD}	–	–	V	CMOS Input
SID58	V_{IL}	Input voltage low threshold	–	–	0.3 × V_{DDD}		CMOS Input
SID241	V_{IH}[3]	LVTTL input, V_{DDD} < 2.7 V	0.7 × V_{DDD}	–	–		–
SID242	V_{IL}	LVTTL input, V_{DDD} < 2.7 V	–	–	0.3 × V_{DDD}		–
SID243	V_{IH}[3]	LVTTL input, $V_{DDD} \geq$ 2.7 V	2.0	–	–		–
SID244	V_{IL}	LVTTL input, $V_{DDD} \geq$ 2.7 V	–	–	0.8		–
SID59	V_{OH}	Output voltage high level	V_{DDD} –0.6	–	–		I_{OH} = 4 mA at 3 V V_{DDD}
SID60	V_{OH}	Output voltage high level	V_{DDD} –0.5	–	–		I_{OH} = 1 mA at 1.8 V V_{DDD}
SID61	V_{OL}	Output voltage low level	–	–	0.6		I_{OL} = 4 mA at 1.8 V V_{DDD}
SID62	V_{OL}	Output voltage low level	–	–	0.6		I_{OL} = 10 mA at 3 V V_{DDD}
SID62A	V_{OL}	Output voltage low level	–	–	0.4		I_{OL} = 3 mA at 3 V V_{DDD}
SID63	R_{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	–
SID64	$R_{PULLDOWN}$	Pull-down resistor	3.5	5.6	8.5		–
SID65	I_{IL}	Input leakage current (absolute value)	–	–	2	nA	25 °C, V_{DDD} = 3.0 V
SID66	C_{IN}	Input capacitance	–	–	7	pF	–
SID67[4]	V_{HYSTTL}	Input hysteresis LVTTL	25	40	–	mV	$V_{DDD} \geq$ 2.7 V
SID68[4]	$V_{HYSCMOS}$	Input hysteresis CMOS	0.05 × V_{DDD}	–	–		V_{DD} < 4.5 V
SID68A[4]	$V_{HYSCMOS5V5}$	Input hysteresis CMOS	200	–	–		V_{DD} > 4.5 V
SID69[4]	I_{DIODE}	Current through protection diode to V_{DD}/V_{SS}	–	–	100	µA	–
SID69A[4]	I_{TOT_GPIO}	Maximum total source or sink chip current	–	–	200	mA	–

Table 5. GPIO AC Specifications
(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID70	T_{RISEF}	Rise time in fast strong mode	2	–	12	ns	3.3 V V_{DDD}, Cload = 25 pF
SID71	T_{FALLF}	Fall time in fast strong mode	2	–	12		3.3 V V_{DDD}, Cload = 25 pF
SID72	T_{RISES}	Rise time in slow strong mode	10	–	60	–	3.3 V V_{DDD}, Cload = 25 pF

Notes
3. V_{IH} must not exceed V_{DDD} + 0.2 V.
4. Guaranteed by characterization.

Table 5. GPIO AC Specifications *(continued)*
(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID73	T_{FALLS}	Fall time in slow strong mode	10	–	60	–	3.3 V V_{DDD}, Cload = 25 pF
SID74	$F_{GPIOUT1}$	GPIO F_{OUT}; 3.3 V ≤ V_{DDD} ≤ 5.5 V Fast strong mode	–	–	33	MHz	90/10%, 25 pF load, 60/40 duty cycle
SID75	$F_{GPIOUT2}$	GPIO F_{OUT}; 1.71 V≤ V_{DDD}≤ 3.3 V Fast strong mode	–	–	16.7		90/10%, 25 pF load, 60/40 duty cycle
SID76	$F_{GPIOUT3}$	GPIO F_{OUT}; 3.3 V ≤ V_{DDD} ≤ 5.5 V Slow strong mode	–	–	7		90/10%, 25 pF load, 60/40 duty cycle
SID245	$F_{GPIOUT4}$	GPIO F_{OUT}; 1.71 V ≤ V_{DDD} ≤ 3.3 V Slow strong mode.	–	–	3.5		90/10%, 25 pF load, 60/40 duty cycle
SID246	F_{GPIOIN}	GPIO input operating frequency; 1.71 V ≤ V_{DDD} ≤ 5.5 V	–	–	48		90/10% V_{IO}

XRES

Table 6. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID77	V_{IH}	Input voltage high threshold	0.7 × V_{DDD}	–	–	V	CMOS Input
SID78	V_{IL}	Input voltage low threshold	–	–	0.3 × V_{DDD}		
SID79	R_{PULLUP}	Pull-up resistor	–	60	–	kΩ	–
SID80	C_{IN}	Input capacitance	–	–	7	pF	–
SID81[5]	$V_{HYSXRES}$	Input voltage hysteresis	–	100	–	mV	Typical hysteresis is 200 mV for V_{DD} > 4.5 V
SID82	I_{DIODE}	Current through protection diode to V_{DD}/V_{SS}	–	–	100	µA	

Table 7. XRES AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID83[5]	$T_{RESETWIDTH}$	Reset pulse width	1	–	–	µs	–
BID194[5]	$T_{RESETWAKE}$	Wake-up time from reset release	–	–	2.7	ms	–

Note
5. Guaranteed by characterization.

Table 8. CTBm Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID283	V_{OUT_1}	power=hi, Iload=10 mA	0.5	–	V_{DDA} -0.5	V	–
SID284	V_{OUT_2}	power=hi, Iload=1 mA	0.2	–	V_{DDA} -0.2		–
SID285	V_{OUT_3}	power=med, Iload=1 mA	0.2	–	V_{DDA} -0.2		–
SID286	V_{OUT_4}	power=lo, Iload=0.1 mA	0.2	–	V_{DDA} -0.2		–
SID288	V_{OS_TR}	Offset voltage, trimmed	–1.0	±0.5	1.0	mV	High mode, input 0 V to V_{DDA}-0.2 V
SID288A	V_{OS_TR}	Offset voltage, trimmed	–	±1	–		Medium mode, input 0 V to V_{DDA}-0.2 V
SID288B	V_{OS_TR}	Offset voltage, trimmed	–	±2	–		Low mode, input 0 V to V_{DDA}-0.2 V
SID290	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–10	±3	10	µV/°C	High mode
SID290A	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–	µV/°C	Medium mode
SID290B	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–		Low mode
SID291	CMRR	DC	70	80	–	dB	Input is 0 V to V_{DDA}-0.2 V, Output is 0.2 V to V_{DDA}-0.2 V
SID292	PSRR	At 1 kHz, 10-mV ripple	70	85	–		V_{DDD} = 3.6 V, high-power mode, input is 0.2 V to V_{DDA}-0.2 V
	Noise						
SID294	VN2	Input-referred, 1 kHz, power = Hi	–	72	–	nV/rtHz	Input and output are at 0.2 V to V_{DDA}-0.2 V
SID295	VN3	Input-referred, 10 kHz, power = Hi	–	28	–		Input and output are at 0.2 V to V_{DDA}-0.2 V
SID296	VN4	Input-referred, 100 kHz, power = Hi	–	15	–		Input and output are at 0.2 V to V_{DDA}-0.2 V
SID297	C_{LOAD}	Stable up to max. load. Performance specs at 50 pF.	–	–	125	pF	–
SID298	SLEW_RATE	Cload = 50 pF, Power = High, V_{DDA} = 2.7 V	6	–	–	V/µs	–
SID299	T_OP_WAKE	From disable to enable, no external RC dominating	–	–	25	µs	–
SID299A	OL_GAIN	Open Loop Gain	–	90	–	dB	
	COMP_MODE	Comparator mode; 50 mV drive, T_{rise}=T_{fall} (approx.)					

Table 8. CTBm Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID300	TPD1	Response time; power=hi	–	150	–	ns	Input is 0.2 V to V_{DDA}-0.2 V
SID301	TPD2	Response time; power=med	–	500	–		Input is 0.2 V to V_{DDA}-0.2 V
SID302	TPD3	Response time; power=lo	–	2500	–		Input is 0.2 V to V_{DDA}-0.2 V
SID303	VHYST_OP	Hysteresis	–	10	–	mV	–
SID304	WUP_CTB	Wake-up time from Enabled to Usable	–	–	25	µs	–
	Deep Sleep Mode	Mode 2 is lowest current range. Mode 1 has higher GBW.					
SID_DS_1	$I_{DD\_HI\_M1}$	Mode 1, High current	–	1400	–	µA	25 °C
SID_DS_2	$I_{DD\_MED\_M1}$	Mode 1, Medium current	–	700	–		25 °C
SID_DS_3	$I_{DD\_LOW\_M1}$	Mode 1, Low current	–	200	–		25 °C
SID_DS_4	$I_{DD\_HI\_M2}$	Mode 2, High current	–	120	–		25 °C
SID_DS_5	$I_{DD\_MED\_M2}$	Mode 2, Medium current	–	60	–		25 °C
SID_DS_6	$I_{DD\_LOW\_M2}$	Mode 2, Low current	–	15	–		25 °C
SID_DS_7	$G_{BW\_HI\_M1}$	Mode 1, High current	–	4	–	MHz	20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_8	$G_{BW\_MED\_M1}$	Mode 1, Medium current	–	2	–		20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_9	$G_{BW\_LOW\_M1}$	Mode 1, Low current	–	0.5	–		20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_10	$G_{BW\_HI\_M2}$	Mode 2, High current	–	0.5	–		20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_11	$G_{BW\_MED\_M2}$	Mode 2, Medium current	–	0.2	–		20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_12	$G_{BW\_Low\_M2}$	Mode 2, Low current	–	0.1	–		20-pF load, no DC load 0.2 V to V_{DDA}-0.2 V
SID_DS_13	$V_{OS\_HI\_M1}$	Mode 1, High current	–	5	–	mV	With trim 25 °C, 0.2 V to V_{DDA}-0.2 V
SID_DS_14	$V_{OS\_MED\_M1}$	Mode 1, Medium current	–	5	–		With trim 25 °C, 0.2 V to V_{DDA}-0.2 V
SID_DS_15	$V_{OS\_LOW\_M2}$	Mode 1, Low current	–	5	–		With trim 25 °C, 0.2 V to V_{DDA}-0.2 V
SID_DS_16	$V_{OS\_HI\_M2}$	Mode 2, High current	–	5	–		With trim 25 °C, 0.2V to V_{DDA}-0.2 V
SID_DS_17	$V_{OS\_MED\_M2}$	Mode 2, Medium current	–	5	–		With trim 25 °C, 0.2 V to V_{DDA}-0.2 V
SID_DS_18	$V_{OS\_LOW\_M2}$	Mode 2, Low current	–	5	–		With trim 25 °C, 0.2 V to V_{DDA}-0.2 V

Table 8. CTBm Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID_DS_19	$I_{OUT\_HI\_M1}$	Mode 1, High current	–	10	–	mA	Output is 0.5 V to V_{DDA}-0.5 V
SID_DS_20	$I_{OUT\_MED\_M1}$	Mode 1, Medium current	–	10	–		Output is 0.5 V to V_{DDA}-0.5 V
SID_DS_21	$I_{OUT\_LOW\_M1}$	Mode 1, Low current	–	4	–		Output is 0.5 V to V_{DDA}-0.5 V
SID_DS_22	$I_{OUT\_HI\_M2}$	Mode 2, High current	–	1	–		
SID_DS_23	$I_{OU\_MED\_M2}$	Mode 2, Medium current	–	1	–		
SID_DS_24	$I_{OU\_LOW\_M2}$	Mode 2, Low current	–	0.5	–		

Comparator

Table 9. Comparator DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID84	$V_{OFFSET1}$	Input offset voltage, Factory trim	–	–	±10	mV	
SID85	$V_{OFFSET2}$	Input offset voltage, Custom trim	–	–	±4		
SID86	V_{HYST}	Hysteresis when enabled	–	10	35		
SID87	V_{ICM1}	Input common mode voltage in normal mode	0	–	V_{DDD}-0.1	V	Modes 1 and 2
SID247	V_{ICM2}	Input common mode voltage in low power mode	0	–	V_{DDD}		
SID247A	V_{ICM3}	Input common mode voltage in ultra low power mode	0	–	V_{DDD}-1.15		V_{DDD} ≥ 2.2 V at –40 °C
SID88	C_{MRR}	Common mode rejection ratio	50	–	–	dB	V_{DDD} ≥ 2.7V
SID88A	C_{MRR}	Common mode rejection ratio	42	–	–		V_{DDD} ≤ 2.7V
SID89	I_{CMP1}	Block current, normal mode	–	–	400	µA	
SID248	I_{CMP2}	Block current, low power mode	–	–	100		
SID259	I_{CMP3}	Block current in ultra low-power mode	–	–	6		V_{DDD} ≥ 2.2 V at –40 °C
SID90	Z_{CMP}	DC Input impedance of comparator	35	–	–	MΩ	

Table 10. Comparator AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID91	TRESP1	Response time, normal mode, 50 mV overdrive	–	38	110	ns	
SID258	TRESP2	Response time, low power mode, 50 mV overdrive	–	70	200		
SID92	TRESP3	Response time, ultra-low power mode, 200 mV overdrive	–	2.3	15	µs	V_{DDD} ≥ 2.2 V at –40 °C

Note
6. Guaranteed by characterization.

Temperature Sensor

Table 11. Temperature Sensor Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID93	TSENSACC	Temperature sensor accuracy	–5	±1	5	°C	–40 to +85 °C

SAR ADC

Table 12. SAR ADC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SAR ADC DC Specifications							
SID94	A_RES	Resolution	–	–	12	bits	
SID95	A_CHNLS_S	Number of channels - single ended	–	–	16		
SID96	A-CHNKS_D	Number of channels - differential	–	–	4		Diff inputs use neighboring I/O
SID97	A-MONO	Monotonicity	–	–	–		Yes
SID98	A_GAINERR	Gain error	–	–	±0.1	%	With external reference
SID99	A_OFFSET	Input offset voltage	–	–	2	mV	Measured with 1-V reference
SID100	A_ISAR	Current consumption	–	–	1	mA	
SID101	A_VINS	Input voltage range - single ended	V_{SS}	–	V_{DDA}	V	
SID102	A_VIND	Input voltage range - differential	V_{SS}	–	V_{DDA}	V	
SID103	A_INRES	Input resistance	–	–	2.2	KΩ	
SID104	A_INCAP	Input capacitance	–	–	10	pF	
SID260	VREFSAR	Trimmed internal reference to SAR	–	–	TBD	V	
SAR ADC AC Specifications							
SID106	A_PSRR	Power supply rejection ratio	70	–	–	dB	
SID107	A_CMRR	Common mode rejection ratio	66	–	–	dB	Measured at 1 V
SID108	A_SAMP	Sample rate	–	–	1	Msps	
SID109	A_SNR	Signal-to-noise and distortion ratio (SINAD)	65	–	–	dB	F_{IN} = 10 kHz
SID110	A_BW	Input bandwidth without aliasing	–	–	A_samp/2	kHz	
SID111	A_INL	Integral non linearity. V_{DD} = 1.71 to 5.5, 1 Msps	–1.7	–	2	LSB	V_{REF} = 1 to V_{DD}
SID111A	A_INL	Integral non linearity. V_{DDD} = 1.71 to 3.6, 1 Msps	–1.5	–	1.7	LSB	V_{REF} = 1.71 to V_{DD}
SID111B	A_INL	Integral non linearity. V_{DD} = 1.71 to 5.5, 500 ksps	–1.5	–	1.7	LSB	V_{REF} = 1 to V_{DD}
SID112	A_DNL	Differential non linearity. V_{DD} = 1.71 to 5.5, 1 Msps	–1	_	2.2	LSB	V_{REF} = 1 to V_{DD}
SID112A	A_DNL	Differential non linearity. V_{DD} = 1.71 to 3.6, 1 Msps	–1	_	2	LSB	V_{REF} = 1.71 to V_{DD}
SID112B	A_DNL	Differential non linearity. V_{DD} = 1.71 to 5.5, 500 ksps	–1	_	2.2	LSB	V_{REF} = 1 to V_{DD}
SID113	A_THD	Total harmonic distortion	–	–	–65	dB	Fin = 10 kHz
SID261	FSARINTREF	SAR operating speed without external reference bypass	_	_	100	ksps	12-bit resolution

CSD and IDAC

Table 13. CSD and IDAC Specifications

SPEC ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SYS.PER#3	VDD_RIPPLE	Max allowed ripple on power supply, DC to 10 MHz	–	–	±50	mV	V_{DD} > 2 V (with ripple), 25 °C T_A, Sensitivity = 0.1 pF
SYS.PER#16	VDD_RIPPLE_1.8	Max allowed ripple on power supply, DC to 10 MHz	–	–	±25	mV	V_{DD} > 1.75V (with ripple), 25 °C T_A, Parasitic Capacitance (C_P) < 20 pF, Sensitivity ≥ 0.4 pF
SID.CSD.BLK	ICSD	Maximum block current	–	–	4000	µA	Maximum block current for both IDACs in dynamic (switching) mode including comparators, buffer, and reference generator
SID.CSD#15	V_{REF}	Voltage reference for CSD and Comparator	0.6	1.2	V_{DDA} - 0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID.CSD#15A	VREF_EXT	External Voltage reference for CSD and Comparator	0.6		V_{DDA} - 0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID.CSD#16	IDAC1IDD	IDAC1 (7-bits) block current	–	–	1750	µA	
SID.CSD#17	IDAC2IDD	IDAC2 (7-bits) block current	–	–	1750	µA	
SID308	VCSD	Voltage range of operation	1.71	–	5.5	V	1.8 V ±5% or 1.8 V to 5.5 V
SID308A	VCOMPIDAC	Voltage compliance range of IDAC	0.6	–	V_{DDA} –0.6	V	V_{DDA} - 0.06 or 4.4, whichever is lower
SID309	IDAC1DNL	DNL	–1	–	1	LSB	
SID310	IDAC1INL	INL	–2	–	2	LSB	INL is ±5.5 LSB for V_{DDA} < 2 V
SID311	IDAC2DNL	DNL	–1	–	1	LSB	
SID312	IDAC2INL	INL	–2	–	2	LSB	INL is ±5.5 LSB for V_{DDA} < 2 V
SID313	SNR	Ratio of counts of finger to noise. Guaranteed by characterization	5	–	–	Ratio	Capacitance range of 5 to 35 pF, 0.1-pF sensitivity. All use cases. V_{DDA} > 2 V.
SID314	IDAC1CRT1	Output current of IDAC1 (7 bits) in low range	4.2	–	5.4	µA	LSB = 37.5-nA typ
SID314A	IDAC1CRT2	Output current of IDAC1(7 bits) in medium range	34	–	41	µA	LSB = 300-nA typ
SID314B	IDAC1CRT3	Output current of IDAC1(7 bits) in high range	275	–	330	µA	LSB = 2.4-µA typ
SID314C	IDAC1CRT12	Output current of IDAC1 (7 bits) in low range, 2X mode	8	–	10.5	µA	LSB = 75-nA typ
SID314D	IDAC1CRT22	Output current of IDAC1(7 bits) in medium range, 2X mode	69	–	82	µA	LSB = 600-nA typ.
SID314E	IDAC1CRT32	Output current of IDAC1(7 bits) in high range, 2X mode	540	–	660	µA	LSB = 4.8-µA typ
SID315	IDAC2CRT1	Output current of IDAC2 (7 bits) in low range	4.2	–	5.4	µA	LSB = 37.5-nA typ
SID315A	IDAC2CRT2	Output current of IDAC2 (7 bits) in medium range	34	–	41	µA	LSB = 300-nA typ
SID315B	IDAC2CRT3	Output current of IDAC2 (7 bits) in high range	275	–	330	µA	LSB = 2.4-µA typ
SID315C	IDAC2CRT12	Output current of IDAC2 (7 bits) in low range, 2X mode	8	–	10.5	µA	LSB = 75-nA typ
SID315D	IDAC2CRT22	Output current of IDAC2(7 bits) in medium range, 2X mode	69	–	82	µA	LSB = 600-nA typ
SID315E	IDAC2CRT32	Output current of IDAC2(7 bits) in high range, 2X mode	540	–	660	µA	LSB = 4.8-µA typ
SID315F	IDAC3CRT13	Output current of IDAC in 8-bit mode in low range	8	–	10.5	µA	LSB = 37.5-nA typ

Table 13. CSD and IDAC Specifications *(continued)*

SPEC ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID315G	IDAC3CRT23	Output current of IDAC in 8-bit mode in medium range	69	–	82	µA	LSB = 300-nA typ
SID315H	IDAC3CRT33	Output current of IDAC in 8-bit mode in high range	540	–	660	µA	LSB = 2.4-µA typ
SID320	IDACOFFSET	All zeroes input	–	–	1	LSB	Polarity set by Source or Sink. Offset is 2 LSBs for 37.5 nA/LSB mode
SID321	IDACGAIN	Full-scale error less offset	–	–	±10	%	
SID322	IDACMISMATCH1	Mismatch between IDAC1 and IDAC2 in Low mode	–	–	9.2	LSB	LSB = 37.5-nA typ
SID322A	IDACMISMATCH2	Mismatch between IDAC1 and IDAC2 in Medium mode	–	–	5.6	LSB	LSB = 300-nA typ
SID322B	IDACMISMATCH3	Mismatch between IDAC1 and IDAC2 in High mode	–	–	6.8	LSB	LSB = 2.4-µA typ
SID323	IDACSET8	Settling time to 0.5 LSB for 8-bit IDAC	–	–	5	µs	Full-scale transition. No external load
SID324	IDACSET7	Settling time to 0.5 LSB for 7-bit IDAC	–	–	5	µs	Full-scale transition. No external load
SID325	CMOD	External modulator capacitor.	–	2.2	–	nF	5-V rating, X7R or NP0 cap

10-bit CapSense ADC

Table 14. 10-bit CapSense ADC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SIDA94	A_RES	Resolution	–	–	10	bits	Auto-zeroing is required every millisecond
SIDA95	A_CHNLS_S	Number of channels - single ended	–	–	16		Defined by AMUX Bus
SIDA97	A-MONO	Monotonicity	–	–	–	Yes	
SIDA98	A_GAINERR	Gain error	–	–	±3	%	In V_{REF} (2.4 V) mode with V_{DDA} bypass capacitance of 10 µF
SIDA99	A_OFFSET	Input offset voltage	–	–	±18	mV	In V_{REF} (2.4 V) mode with V_{DDA} bypass capacitance of 10 µF
SIDA100	A_ISAR	Current consumption	–	–	0.25	mA	
SIDA101	A_VINS	Input voltage range - single ended	V_{SSA}	–	V_{DDA}	V	
SIDA103	A_INRES	Input resistance	–	2.2	–	KΩ	
SIDA104	A_INCAP	Input capacitance	–	20	–	pF	
SIDA106	A_PSRR	Power supply rejection ratio	–	60	–	dB	In V_{REF} (2.4 V) mode with V_{DDA} bypass capacitance of 10 µF
SIDA107	A_TACQ	Sample acquisition time	–	1	–	µs	
SIDA108	A_CONV8	Conversion time for 8-bit resolution at conversion rate = Fhclk/(2^(N+2)). Clock frequency = 48 MHz.	–	–	21.3	µs	Does not include acquisition time. Equivalent to 44.8 ksps including acquisition time.
SIDA108A	A_CONV10	Conversion time for 10-bit resolution at conversion rate = Fhclk/(2^(N+2)). Clock frequency = 48 MHz.	–	–	85.3	µs	Does not include acquisition time. Equivalent to 11.6 ksps including acquisition time.

Memory

Table 24. Flash DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID173	V_{PE}	Erase and program voltage	1.71	–	5.5	V	–

Table 25. Flash AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID174	$T_{ROWWRITE}$[10]	Row (block) write time (erase and program)	–	–	20	ms	Row (block) = 256 bytes
SID175	$T_{ROWERASE}$[10]	Row erase time	–	–	16		–
SID176	$T_{ROWPROGRAM}$[10]	Row program time after erase	–	–	4		–
SID178	$T_{BULKERASE}$[10]	Bulk erase time (64 KB)	–	–	35		–
SID180[11]	$T_{DEVPROG}$[10]	Total device program time	–	–	7	Seconds	–
SID181[11]	F_{END}	Flash endurance	100 K	–	–	Cycles	–
SID182[11]	F_{RET}	Flash retention. $T_A \leq 55$ °C, 100 K P/E cycles	20	–	–	Years	–
SID182A[11]	–	Flash retention. $T_A \leq 85$ °C, 10 K P/E cycles	10	–	–		–
SID256	TWS48	Number of Wait states at 48 MHz	2	–	–		CPU execution from Flash
SID257	TWS24	Number of Wait states at 24 MHz	1	–	–		CPU execution from Flash

System Resources

Power-on Reset (POR)

Table 26. Power On Reset (PRES)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.CLK#6	SR_POWER_UP	Power supply slew rate	1	–	67	V/ms	At power-up
SID185[11]	$V_{RISEIPOR}$	Rising trip voltage	0.80	–	1.5	V	–
SID186[11]	$V_{FALLIPOR}$	Falling trip voltage	0.70	–	1.4		–

Table 27. Brown-out Detect (BOD) for V_{CCD}

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID190[11]	$V_{FALLPPOR}$	BOD trip voltage in active and sleep modes	1.48	–	1.62	V	–
SID192[11]	$V_{FALLDPSLP}$	BOD trip voltage in Deep Sleep	1.11	–	1.5		–

Notes
10. It can take as much as 20 milliseconds to write to Flash. During this time the device should not be Reset, or Flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.
11. Guaranteed by characterization.

SWD Interface

Table 28. SWD Interface Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID213	F_SWDCLK1	3.3 V ≤ V_{DD} ≤ 5.5 V	–	–	14	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID214	F_SWDCLK2	1.71 V ≤ V_{DD} ≤ 3.3 V	–	–	7		SWDCLK ≤ 1/3 CPU clock frequency
SID215[12]	T_SWDI_SETUP	T = 1/f SWDCLK	0.25*T	–	–	ns	–
SID216[12]	T_SWDI_HOLD	T = 1/f SWDCLK	0.25*T	–	–		–
SID217[12]	T_SWDO_VALID	T = 1/f SWDCLK	–	–	0.5*T		–
SID217A[12]	T_SWDO_HOLD	T = 1/f SWDCLK	1	–	–		–

Internal Main Oscillator

Table 29. IMO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID218	I_{IMO1}	IMO operating current at 48 MHz	–	–	250	µA	–
SID219	I_{IMO2}	IMO operating current at 24 MHz	–	–	180	µA	–

Table 30. IMO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID223	$F_{IMOTOL1}$	Frequency variation at 24, 32, and 48 MHz (trimmed)	–	–	±2	%	
SID226	$T_{STARTIMO}$	IMO startup time	–	–	7	µs	–
SID228	$T_{JITRMSIMO2}$	RMS jitter at 24 MHz	–	145	–	ps	–

Internal Low-Speed Oscillator

Table 31. ILO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID231	I_{ILO1}	ILO operating current	–	0.3	1.05	µA	–

Table 32. ILO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID234[12]	$T_{STARTILO1}$	ILO startup time	–	–	2	ms	–
SID236[12]	$T_{ILODUTY}$	ILO duty cycle	40	50	60	%	–
SID237	$F_{ILOTRIM1}$	ILO frequency range	20	40	80	kHz	–

Note
12. Guaranteed by design.

Smart I/O

Table 38. Smart I/O Pass-through Time (Delay in Bypass Mode)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID252	PRG_BYPASS	Max delay added by Smart I/O in bypass mode	–	–	1.6	ns	

CAN

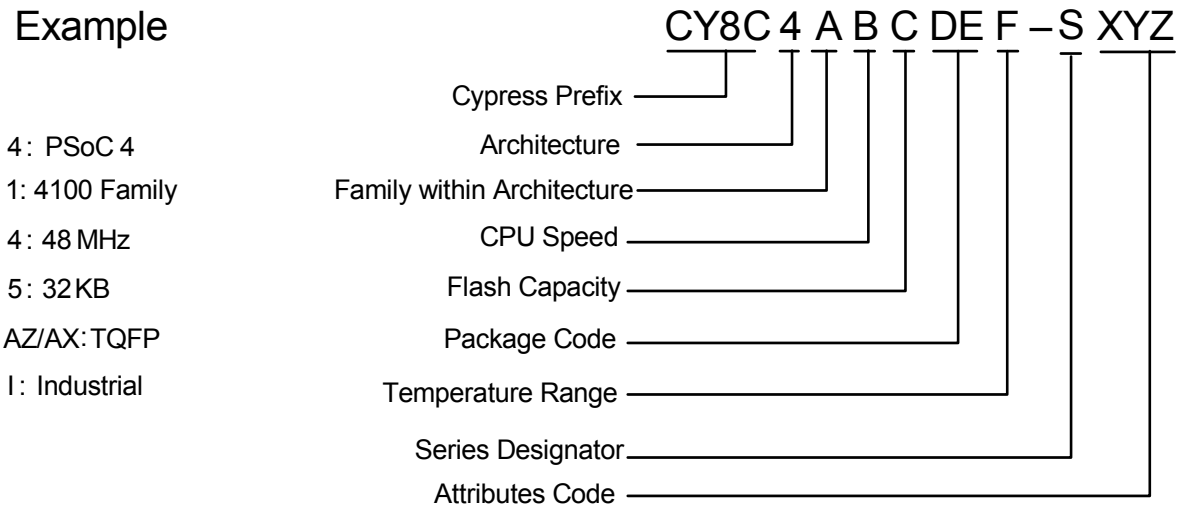
Table 39. CAN Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID420	IDD_CAN	Block current consumption	–	–	200	µA	
SID421	CAN_bits	CAN Bit rate	–	–	1	Mbps	Min 8-MHZ clock

The nomenclature used in the preceding table is based on the following part numbering convention:

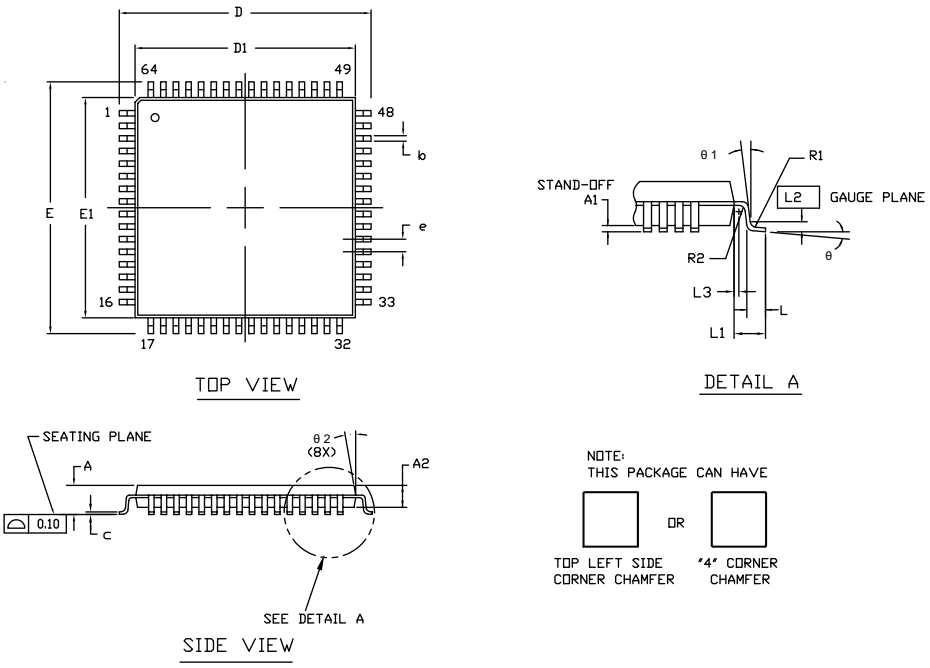
Field	Description	Values	Meaning
CY8C	Cypress Prefix		
4	Architecture	4	PSoC 4
A	Family	1	4100 Family
B	CPU Speed	2	24 MHz
		4	48 MHz
C	Flash Capacity	4	16 KB
		5	32 KB
		6	64 KB
		7	128 KB
DE	Package Code	AX	TQFP (0.8-mm pitch)
		AZ	TQFP (0.5-mm pitch)
		LQ	QFN
		PV	SSOP
		FN	CSP
F	Temperature Range	I	Industrial
S	Series Designator	S	PSoC 4 S-Series
		M	PSoC 4 M-Series
		L	PSoC 4 L-Series
		BL	PSoC 4 BLE-Series
XYZ	Attributes Code	000-999	Code of feature set in the specific family

The following is an example of a part number:



Package Diagrams

Figure 7. 64-pin TQFP Package (0.8-mm Pitch) Outline



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	—	—	1.60
A1	0.05	—	0.15
A2	1.35	1.40	1.45
D	15.75	16.00	16.25
D1	13.95	14.00	14.05
E	15.75	16.00	16.25
E1	13.95	14.00	14.05
R1	0.08	—	0.20
R2	0.08	—	0.20
θ	0°	—	7°
θ1	0°	—	—
θ2	11°	12°	13°
c	—	—	0.20
b	0.30	0.35	0.40
L	0.45	0.60	0.75
L1	1.00 REF		
L2	0.25 BSC		
L3	0.20	—	—
e	0.80 TYP		

NOTE:
1. JEDEC STD REF MS-026
2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.0098 in (0.25 mm) PER SIDE BODY LENGTH DIMENSIONS ARE MAX PLASTIC BODY SIZE INCLUDING MOLD MISMATCH
3. DIMENSIONS IN MILLIMETERS

51-85046 *H

Acronyms

Table 44. Acronyms Used in this Document

Acronym	Description
abus	analog local bus
ADC	analog-to-digital converter
AG	analog global
AHB	AMBA (advanced microcontroller bus architecture) high-performance bus, an Arm data transfer bus
ALU	arithmetic logic unit
AMUXBUS	analog multiplexer bus
API	application programming interface
APSR	application program status register
Arm®	advanced RISC machine, a CPU architecture
ATM	automatic thump mode
BW	bandwidth
CAN	Controller Area Network, a communications protocol
CMRR	common-mode rejection ratio
CPU	central processing unit
CRC	cyclic redundancy check, an error-checking protocol
DAC	digital-to-analog converter, see also IDAC, VDAC
DFB	digital filter block
DIO	digital input/output, GPIO with only digital capabilities, no analog. See GPIO.
DMIPS	Dhrystone million instructions per second
DMA	direct memory access, see also TD
DNL	differential nonlinearity, see also INL
DNU	do not use
DR	port write data registers
DSI	digital system interconnect
DWT	data watchpoint and trace
ECC	error correcting code
ECO	external crystal oscillator
EEPROM	electrically erasable programmable read-only memory
EMI	electromagnetic interference
EMIF	external memory interface
EOC	end of conversion
EOF	end of frame
EPSR	execution program status register
ESD	electrostatic discharge

Table 44. Acronyms Used in this Document *(continued)*

Acronym	Description
ETM	embedded trace macrocell
FIR	finite impulse response, see also IIR
FPB	flash patch and breakpoint
FS	full-speed
GPIO	general-purpose input/output, applies to a PSoC pin
HVI	high-voltage interrupt, see also LVI, LVD
IC	integrated circuit
IDAC	current DAC, see also DAC, VDAC
IDE	integrated development environment
I^2C, or IIC	Inter-Integrated Circuit, a communications protocol
IIR	infinite impulse response, see also FIR
ILO	internal low-speed oscillator, see also IMO
IMO	internal main oscillator, see also ILO
INL	integral nonlinearity, see also DNL
I/O	input/output, see also GPIO, DIO, SIO, USBIO
IPOR	initial power-on reset
IPSR	interrupt program status register
IRQ	interrupt request
ITM	instrumentation trace macrocell
LCD	liquid crystal display
LIN	Local Interconnect Network, a communications protocol.
LR	link register
LUT	lookup table
LVD	low-voltage detect, see also LVI
LVI	low-voltage interrupt, see also HVI
LVTTL	low-voltage transistor-transistor logic
MAC	multiply-accumulate
MCU	microcontroller unit
MISO	master-in slave-out
NC	no connect
NMI	nonmaskable interrupt
NRZ	non-return-to-zero
NVIC	nested vectored interrupt controller
NVL	nonvolatile latch, see also WOL
opamp	operational amplifier
PAL	programmable array logic, see also PLD

Table 44. Acronyms Used in this Document *(continued)*

Acronym	Description
PC	program counter
PCB	printed circuit board
PGA	programmable gain amplifier
PHUB	peripheral hub
PHY	physical layer
PICU	port interrupt control unit
PLA	programmable logic array
PLD	programmable logic device, see also PAL
PLL	phase-locked loop
PMDD	package material declaration data sheet
POR	power-on reset
PRES	precise power-on reset
PRS	pseudo random sequence
PS	port read data register
PSoC®	Programmable System-on-Chip™
PSRR	power supply rejection ratio
PWM	pulse-width modulator
RAM	random-access memory
RISC	reduced-instruction-set computing
RMS	root-mean-square
RTC	real-time clock
RTL	register transfer language
RTR	remote transmission request
RX	receive
SAR	successive approximation register
SC/CT	switched capacitor/continuous time
SCL	I^2C serial clock
SDA	I^2C serial data
S/H	sample and hold
SINAD	signal to noise and distortion ratio
SIO	special input/output, GPIO with advanced features. See GPIO.
SOC	start of conversion
SOF	start of frame
SPI	Serial Peripheral Interface, a communications protocol
SR	slew rate
SRAM	static random access memory
SRES	software reset
SWD	serial wire debug, a test protocol

Table 44. Acronyms Used in this Document *(continued)*

Acronym	Description
SWV	single-wire viewer
TD	transaction descriptor, see also DMA
THD	total harmonic distortion
TIA	transimpedance amplifier
TRM	technical reference manual
TTL	transistor-transistor logic
TX	transmit
UART	Universal Asynchronous Transmitter Receiver, a communications protocol
UDB	universal digital block
USB	Universal Serial Bus
USBIO	USB input/output, PSoC pins used to connect to a USB port
VDAC	voltage DAC, see also DAC, IDAC
WDT	watchdog timer
WOL	write once latch, see also NVL
WRES	watchdog timer reset
XRES	external reset I/O pin
XTAL	crystal